## **ACIS Gain Corrections with Cas A + Perseus**



- Time-Dependent Gain Changes
- Motivation to use AP Sources
  - Perseus 6.7 keV Fe
  - Cas A 1.8 keV Si
- "Fully Illuminating" CCD with Maths
- Accuracy Expectation / Future



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## **ACIS Time-Dependent Gain – CTI Effects**

#### TGain CALDB files account for:

- CTI time-dependence (solar cycle / cosmic rays, electronic drift)
- CTI energy dependence  $\rightarrow$  CTI increases non-linearly with energy
- CTI spatial dependence → CTI increases with row number due to # of charge traps that event charge travels through to readout
- CTI CALDB files + CTI corrector algorithm in acis\_process\_events tool account for:
  - CTI temperature dependence → CTI increases with FP\_TEMP



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# < 2024 ACIS TGain Correction

#### < 2024 Method

- <sup>55</sup>Fe produces bright AI, Ti, Mn lines (ECS), fully illuminating ACIS-I and ACIS-S
- Measure pulse height amplitude (PHA, an ADU unit) line center for bright Al-Kα, Ti-Kα, and Mn-Kα line positions
- dPHA = PHA shift from year 2000 line centers
- Repeat for each 32x column, use dPHA @ Al/Ti/Mn to fit for energy dependence





## Perseus Isolated 6.7keV Fe-Heα

- 10 ksec Obs x6 chips (primary imaging CCDs: ACIS-I, S2/3)
- 1x per year
- Extended emission, simple spectrum with bright & isolated Fe @ 6.7 keV

#### Procedure

- Fit Fe LineE in 32x128y chip(x,y) tiles
- dE = measured LineE Fe\_baseline
- Convert dE → dPHA (shift in PHA) units using CALDB DETGAIN (eV vs PHA)

#### Result

• dPHA(chip X,Y) @ 6.7 keV

ACIS 12 Illumination

HITOMI Spectrum





# Cas A 1.856keV Si-He $\alpha$

- 1 ksec Obs x6 chips (I0/1/2, S1/2/4), 2 ksec Obs I3 and S3
- Extended emission
  - ~50 32x128 tiles with counts >100 in Si line
- ... Bulk motion complications ~ -20 to +30 eV (-3,000 to +5,000 km/sec)
  - Early epoch fits for "baseline" Si LineE per tile
  - dE = measured LineE Si\_baseline





# Cas A 1.856keV Si-He $\alpha$

- 1 ksec Obs x6 chips (I0/1/2, S1/2/4), 2 ksec Obs I3 and S3
- Extended emission
  - ~50 32x128 tiles with counts >100 in Si line
- ... Bulk motion complications
- ... Spectrum spatial variation complications  $\rightarrow$  fit in sky coords, then convert back to chip coords
- ... Complicated analysis before obtaining
  - dPHA(chip X,Y) @ 1.856 keV





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Deep S3 GRADED Mode for Baseline Si LineE / tile

# Filling in the Illumination Gaps – Applying PCA

- Use Principle Component Analysis [PCA] to scale TGain spatial structure using Si positions where Si is bright enough to measure
- Prep:
  - Convert TGain pattern from each epoch to 256x1 array (dPHA array of 32x128 regions)
  - PCA accurately describes spatial pattern with 5 components (base vectors)
  - 1<sup>st</sup> components describes largest variations ex. node boundaries
  - Remaining components describe decreasingly important modifications to recreate the structure
- Spatial structure for any given TGain epoch can be recreated with only a few uniquely scaled PCA components







# Filling in the Illumination Gaps – Applying PCA

- Scaling factors calculated from tiles where Si is bright enough to measure dPHA (LineE shift)
  - by number of tiles measurements return by accuracy filling the missing unmeasured chip tiles



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slide 8

# **Filling in the Illumination Gaps**

- Scaling factors calculated from tiles with available measurements
  - 💩 number of tiles measurements return 💩 accuracy filling the missing unmeasured chip tiles



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chipX

## **ACIS Gain Accuracy**

**Cas A + Perseus = TGain Calibration Method for the next** vears of Chandra

ACIS S0/S5 (primarily gratings use): TGain scaled to by S2 ACIS S1/S4 (secondary imaging): Energy dependence fixed to historic values (reduced higher-energy accuracy)

ACIS-I, S2/3/4 (primary imaging) Expectation 68% of 32x128y tiles within: Previously with strong ECS measurements:

~0.6% >0.3%



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